PART ONE: General description				
Nitride Process name Udo Lang Author	Process Code Contact Information (Email)	07/12/00 Last Update		
. General description of process				

PART TWO: Details

RIE Etching			
Pressure Set	185	Oxygen Set	0
RF Power Set	105	CHF3 Set	0
End Point Set	900	SF6 Set	55
Process Time	47		
Base Pressure Set	min 150		

PART THREE: General Comments				
	Etch rate – Approx. 200 (nm/min)			